

Rev.D Oct.-2015

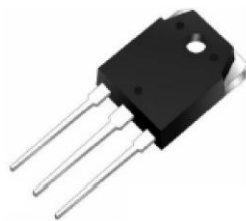
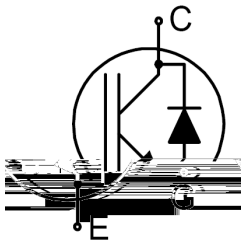
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Insulated-Gate Bipolar Transistor in a TO-3P Plastic Package.

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Low gate charge,, Low saturation voltage ,Positive temperature coefficient, RoHS product.

General purpose inverter, Frequency converters, Induction Heating(IH), Uninterrupted Power Supply(UPS).



PIN1 Gate PIN 2 Collector PIN 3 Emitter

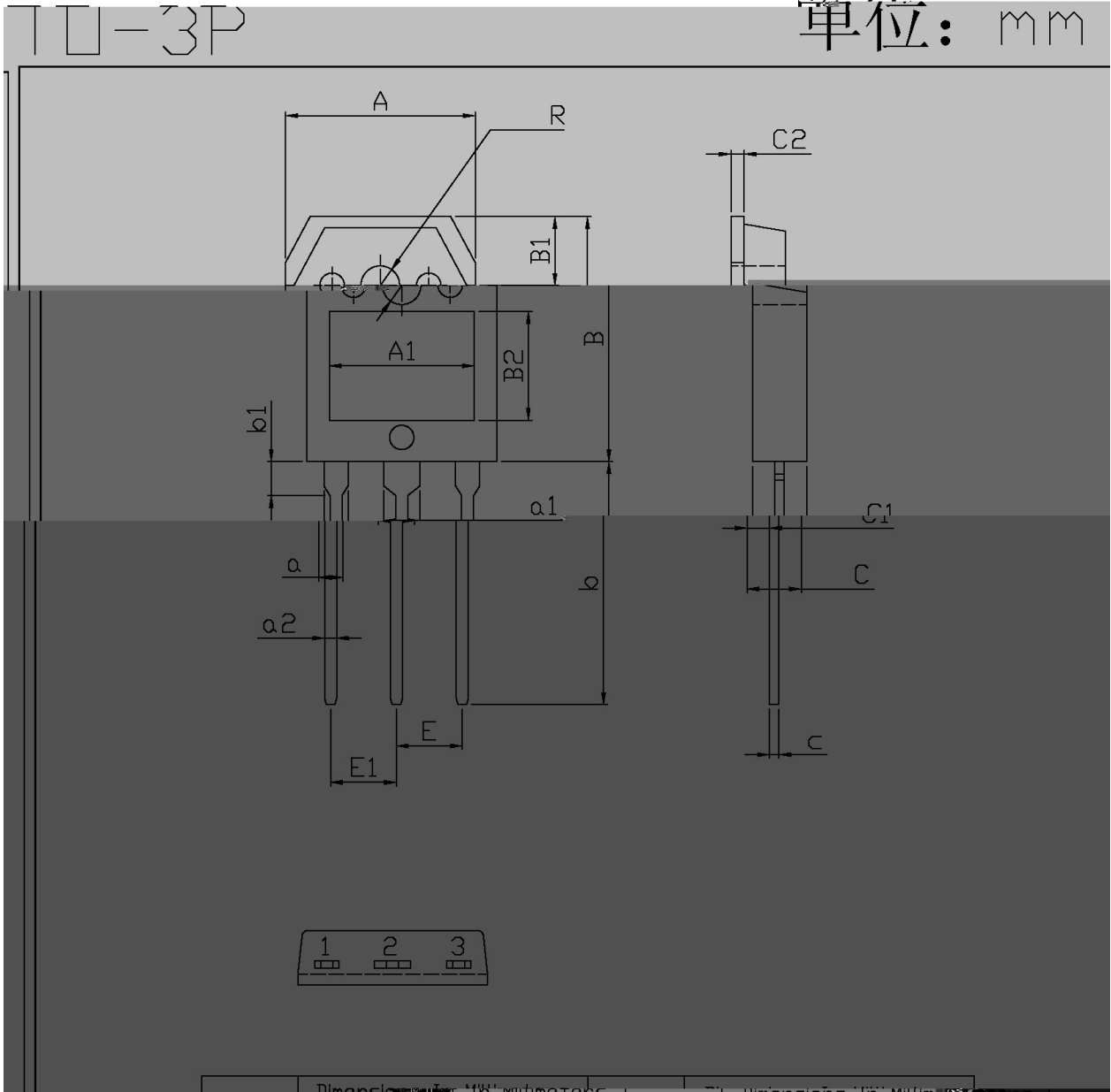
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	1200	V
Gate-emitter voltage	V_{GES}	± 20	V
Collector current	I_C	50	A
Collector current@ $T_C=100^\circ\text{C}$		25	A
Collector peak current, T_P limited by T_{JMAX}	I_{CM}	75	A
Diode forward current@ $T_C=100^\circ\text{C}$	I_F	25	A
Diode maximum forward current	I_{FM}	75	A
Power dissipation($T_C=25^\circ\text{C}$)	P_D	312	W
Power dissipation($T_C=100^\circ\text{C}$)		125	W
Operating junction and storage temperature range	T_J, T_{stg}	-55~150	$^\circ\text{C}$
Maximum temperature for soldering	T_L	300	$^\circ\text{C}$
IGBT thermal resistance,junction-case	$R_{th(j-c)}$	0.4	$^\circ\text{C/W}$
Diode thermal resistance,junction-case	$R_{th(j-C)}$	2	$^\circ\text{C/W}$
Thermal resistance,junction-ambient	$R_{th(j-a)}$	40	$^\circ\text{C/W}$

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V_{CES}	$V_{GE}=0V$	$I_{CE}=250\mu A$	1200	-	-	V
Zero gate voltage Collector current	I_{CES}	$V_{GE}=0V$	$V_{CE}=1200V$	-	-	1	mA
Gate-body leakage current	I_{GES}	$V_{GE}=\pm 20V$	$V_{CE}=0V$	-	-	± 250	nA
Gate threshold voltage	$V_{GE(th)}$	$I_C=15Ma$	$V_{CE}=V_{GE}$	3.5	-	7.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=25A$	$V_{GE}=15V$	-	2.1	2.5	V
Input capacitance	C_{ies}	$V_{CE}=25V$ $f=1MHz$	$V_{GE}=0V$	-	3430	-	pF
Output capacitance	C_{oes}			-	87	-	
Reverse transfer capacitance	C_{res}			-	206	-	

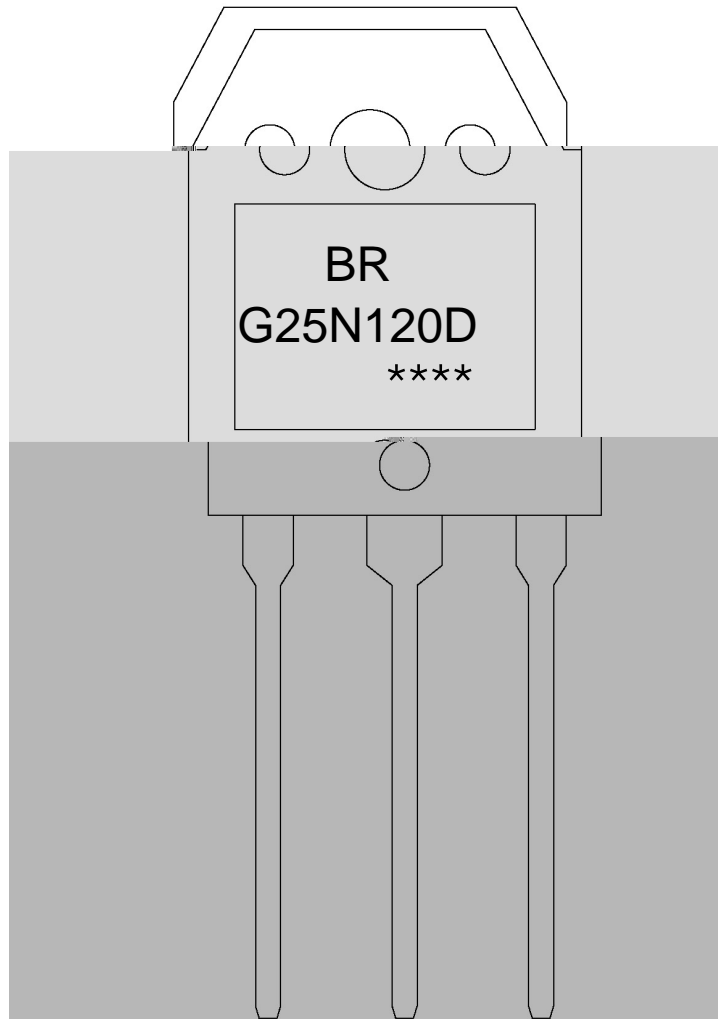
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-on delay time	$t_{d(ON)}$	$V_{CE}=600V$ $I_C=25A$ $R_G=10\Omega$ $V_{GE}=15V$ Inductive Load	-	42	-	ns
Rise time	t_r		-	36	-	
Turn-off delay time	$t_{d(OFF)}$		-	224	-	
Fall time	t_f		-	314	-	
Turn-On Switching Loss	E_{on}		-	1.1	2.2	mJ
Turn-Off Switching Loss	E_{off}		-	1.3	1.5	
Total Switching Loss	E_{ts}		-	2.2	3.6	
Total gate charge	Q_G	$V_{CE}=600V$ $I_C=25A$ $V_{GE}=15V$	-	177	274	nC
Gate-emitter charge	Q_{G-E}		-	16	26	
Gate-collector charge	Q_{G-C}		-	61	94	
Diode forward voltage	V_F	$I_F=25A$	-	1.5	2.7	V
Reverse recovery time	T_{rr}	$I_F=25A$ $di/dt=200A/\mu S$	-	535	585	ns
Diode Peak Reverse Recovery Current	I_{rr}		-	43	85	A
Reverse recovery charge	Q_{rr}		-	13	15	μC

单位: mm



Dimensions in Millimeters / 尺寸在毫米

Symbol	Dimensions in Millimeters	Symbol	Dimensions in Millimeters
A1	12.0	C2	1.4
b	3.0	c	0.5
b1	3.0		
a	1.5		
a1	2.8		



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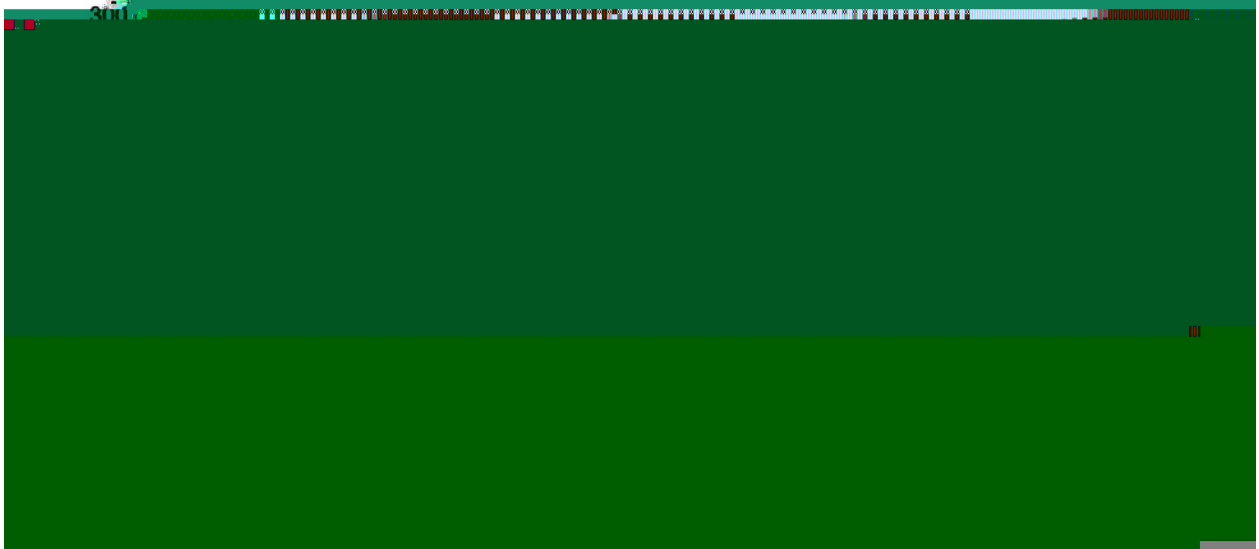
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Note:

BR: Company Code.

G25N120D: Product Type.

****: Lot No. Code, code change with Lot No.



1	25	150	60	90sec;	Note:	1.Preheating:25~150 , Time:60~90sec.
2	255..5		5..0.5sec;		2.Peak Temp.:255..5 , Duration:5..0.5sec.	
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.	

270..5 10..1 sec. Temp.:270±5℃ Time:10±1 sec

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-3P	30	15	450	5	2250	497.5×46×8	555×164×50	575 290 180